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Fabrication of high contrast gratings for the spectrum splitting dispersive element in a concentrated photovoltaic system --Manuscript Draft--

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Abstract:	High contrast gratings are designed and fabricated and its application is proposed in a parallel spectrum splitting dispersive element that can improve the solar conversion efficiency of a concentrated photovoltaic system. The proposed system will also lower the solar cell cost in the concentrated photovoltaic system by replacing the expensive tandem solar cells with the cost-effective single junction solar cells. The structures and the parameters of high contrast gratings for the dispersive elements were numerically optimized. The large-area fabrication of high contrast gratings was experimentally demonstrated using nanoimprint lithography and dry etching. The quality of grating material and the performance of the fabricated device were both experimentally characterized. By analyzing the measurement results, the possible side effects from the fabrication processes are discussed and several methods that have the potential to improve the fabrication processes are proposed, which can help to increase the optical efficiency of the fabricated devices.
Author Comments:	Dear Dr. Nam Nguyen, Many thanks for your letter of Jan. 29th 2015, with the editor's and reviewers' comments. We have carefully reviewed all their remarks and took them all into account. We believe that the amended manuscript is suitable for publication in JoVE. Given the urgency and timeliness nature of JoVE, we would appreciate to have your final decision at your earliest convenience. In addition, we provide below detailed responses to address those comments. Please let me know if you have any further comments. Sincerely yours,

	Yuhan Yao, He Liu and Wei Wu Department of Electrical Engineering, University of Southern California
Additional Information:	
Question	Response
If this article needs to be "in-press" by a certain date to satisfy grant requirements, please indicate the date below and explain in your cover letter.	
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Dear Dr. Nam Nguyen,

Many thanks for your letter of Jan. 29th 2015, with the editor's and reviewers' comments. We have carefully reviewed all their remarks and took them all into account. We believe that the amended manuscript is suitable for publication in JoVE. Given the urgency and timeliness nature of JoVE, we would appreciate to have your final decision at your earliest convenience.

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Sincerely yours,

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Department of Electrical Engineering, University of Southern California

Editorial comments:

1. Please take this opportunity to thoroughly proofread the manuscript to ensure that there are no spelling or grammar issues. The JoVE editor will not copy-edit your manuscript and any errors in the submitted revision may be present in the published version.

Please watch for missing periods at the end of sentences. Also, there are numerous missing articles as well: a, an, the, of, etc.

We have proofread the manuscript for spelling or grammar errors.

2. For volumes of the resist used, please define a "drop".

20 drops = 1 mL. We have added the definition to the protocol.

3. 1.1.6 / 1.2.4 - What pressure must the desiccator be pumped down to?

-30 inHg. We have added the definition to the corresponding steps in the protocol.

Reviewers' Comments:

Review #1:

1. In the protocol, deposition of TiO₂ was not included. Since this is the key material for the device to be fabricated, a procedure of depositing this material should also be included in the protocol.

We have added the protocol of TiO₂ deposition to the protocol.

2. In real application, sunlight is focused on the dispersive element within a certain angle. What is reflectance of the device for sunlight slightly off from the normal incidence direction?

We added the following discussion to the paper. Due to its high index contrast between the grating and substrate, the high contrast grating has good angle independence. Unlike diffraction gratings, high contrast grating has similar reflectance when the incidence angle is less than 15°.

3. The fabricated device achieves a peak reflectance of about 60%. Since a significant amount of light is not reflected by this device, could the authors comment its implication on the overall efficiency of the concentrated photovoltaic device?

Generally speaking, the overall efficiency is the product of the optical efficiency and the solar cell conversion efficiency. Since the peak is about 60%, the overall efficiency will be 40% lower than expected value (40% for four-junction spectrum splitting). In order to achieve a higher overall efficiency, the fabrication process should be further optimized to increase the peak reflectance, which has been discussed in our paper.

Reviewer #2:

In the introduction, the authors stated that the designed dispersive element can be applied in reflective CPV system without prior discussion about the objective of the paper or any brief description for the proposed method. Then they describe the detailed steps. It would be informative for the reader to include a few lines in the introduction about the objective of the work and how the dispersive element will be designed and fabricated before stating the steps in bullets.

Thank you for your comments. We have added more background information at the beginning of the introduction.

Reviewer #3:

1. Specifically what can be adjusted in the dry etching recipes that would give a better etching profile?

We have added the following discussion in the paper. A better etching profile can be achieved by adjusting the combination of gases (C_4F_8 , SF_6 and O_2) to balance the etching and re-deposition process for a straighter side wall.

2. The roughness from the nano-imprint and lift-off process is inherent. What specifically can be done to improve this?

You are absolutely correct. Since nanoimprint is a sub-10nm fabrication technology, the roughness from the master mold will be inherited. To reduce the roughness, we should make a master mold with smoother edges. Various smoothing technologies have been reported. For example, smooth edge can be achieved by thermal process* or chemical anisotropic etching (e.g. KOH to etch silicon).

*Yu, Zhaoning, et al. "Fabrication of nanoscale gratings with reduced line edge roughness using nanoimprint lithography." *Journal of Vacuum Science & Technology B* 21.5 (2003): 2089-2092.

TITLE:

Fabrication of high contrast gratings for the spectrum splitting dispersive element in a concentrated photovoltaic system

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KEYWORDS:

Parallel spectrum splitting, dispersive element, high contrast grating, concentrated photovoltaic system, nanoimprint lithography, reactive ion etching

SHORT ABSTRACT:

The fabrication of high contrast gratings as the parallel spectrum splitting dispersive element in a concentrated photovoltaic system is demonstrated. Fabrication processes including nanoimprint lithography, TiO₂ sputtering and reactive ion etching are described. Reflectance measurement results are used to characterize the optical performance.

LONG ABSTRACT:

High contrast gratings are designed and fabricated and its application is proposed in a parallel spectrum splitting dispersive element that can improve the solar conversion efficiency of a concentrated photovoltaic system. The proposed system will also lower the solar cell cost in the concentrated photovoltaic system by replacing the expensive tandem solar cells with the cost-effective single junction solar cells. The structures and the parameters of high contrast gratings for the dispersive elements were numerically optimized. The large-area fabrication of high

contrast gratings was experimentally demonstrated using nanoimprint lithography and dry etching. The quality of grating material and the performance of the fabricated device were both experimentally characterized. By analyzing the measurement results, the possible side effects from the fabrication processes are discussed and several methods that have the potential to improve the fabrication processes are proposed, which can help to increase the optical efficiency of the fabricated devices.

INTRODUCTION:

Our modern society will not survive without moving a significant portion of energy consumption to renewable energy sources. To make this happen, we have to find a way to harvest renewable energy at a cost lower than petroleum-based energy sources in the near future. Solar energy is the most abundant renewable energy on earth. Despite that a lot of progresses have been made in solar energy harvesting, it is still very challenging to compete with petroleum-based energy sources. Improving the efficiency of solar cells is one of the most efficient ways to lower the system cost of solar energy harvesting.

Optical lenses and dish reflectors are usually used in most concentrated photovoltaic (CPV) systems¹ to achieve a high concentration of solar power incidence on the small-area solar cells, so it is economically viable to exploit expensive tandem multi-junction solar cells² in CPV systems, and to maintain a reasonable cost at the same time. However, for most non-concentrated photovoltaic systems, which usually require a large-area installment of solar cells, the high-cost tandem solar cells cannot be incorporated, although they usually have a broader solar spectrum response and a higher overall conversion efficiency than the single junction solar cells³.

Recently, with the help of the parallel spectrum splitting optics (i.e. dispersive element), the parallel spectrum splitting photovoltaic technology⁴ has made it possible that a similar or better spectrum coverage and conversion efficiency can be achieved without using the expensive tandem solar cells. The solar spectrum can be split into different bands and each band can be absorbed and converted to electricity by the specialized single-junction solar cells. In this way, the expensive tandem solar cells in CPV systems can be replaced by a parallel distribution of single-junction solar cells without any compromise on the performance.

The dispersive element that was designed in this report can be applied in a reflective CPV system (which is based on dish reflectors) to realize parallel spectrum splitting for the improved solar-electricity conversion efficiency and reduced cost. Multilayer high contrast gratings (HCG)⁵ is used as the dispersive element by designing each layer of HCG to work as an optical band reflector. The structures and parameters of the dispersive element are numerically optimized. Moreover, the fabrication of high contrast gratings for the dispersive element by using dielectric (TiO₂) sputtering, nanoimprint lithography⁶ and reactive ion etching is studied and demonstrated.

PROTOCOL:

1. Prepare the blank Polydimethylsiloxane (PDMS) substrate for nanoimprint mold

1.1) Silicon wafer treatment process

1.1.1) Clean a 4-inch silicon wafer by rinsing with acetone, methanol and isopropanol.

1.1.2) Blow it dry using the nitrogen gun.

1.1.3) Clean it using piranha solution (3:1 mixture of sulfuric acid with 30% hydrogen peroxide) by soaking inside for 15 min.

1.1.4) Rinse it with DI water. Blow dry using the nitrogen gun.

1.1.5) Place the wafer in a glass desiccator. Add a drop (20 drops = 1 mL) of releasing agent (Trichlorosilane) into the desiccator.

1.1.6) Pump down the desiccator until the gauge reads -762 Torr and wait for 5 h.

1.1.7) Take the wafer out, which has been treated with releasing agent.

1.2) Preparation of PDMS film (used as mold in nanoimprint)

1.2.1) Weigh 10 g of silicone elastomer base and 1 g of curing agent.

1.2.2) Add them in the same glass beaker.

1.2.3) Stir and mix with a glass rod for 5 min.

1.2.4) Put the mixture into a vacuum desiccator until the gauge reads -762 Torr to pump out all the trapped air bubbles.

1.2.5) Spread them evenly onto the treated 4-inch silicon wafer.

1.2.6) Bake the wafer with PDMS on top in the vacuum oven for 7 h at 80 °C to cure the PDMS film.

2. Prepare the nanoimprint mold (duplication from the master mold)

2.1) Spin twelve drops (20 drops = 1 mL) of UV curable resist (15.2%) on a clean blank silicon wafer for 30 s at 1500 rpm.

2.2) Carefully peel a piece of PDMS film off the treated silicon wafer.

2.3) Put the PDMS film onto the UV curable resist and let it absorb the UV resist for 5 min then

peel it off.

2.4) Repeat 2.1 - 2.3 on the same PDMS film for two times. Absorb the UV resist for 3 min and 1 min respectively.

2.5) Place the PDMS film (after three-time UV resist absorption) onto a silicon master mold.

2.6) Put it into a chamber with nitrogen environment.

2.7) Turn on UV lamp to cure the sample for 5 min.

2.8) Peel off the PDMS film. The cured UV resist on the PDMS will keep the negative pattern of the master mold.

2.9) Use RF O₂ plasma to treat the PDMS mold. (RF power: 30 W, pressure: 260 mTorr, time: 1 min)

2.10) Place the PDMS mold in a vacuum chamber with one drop (20 drops = 1 mL) of releasing agent for 2 h.

3. Nanoimprint pattern transfer

3.1) Spin eight drops (20 drops = 1 mL) of PMMA (996k, 3.1%) on the substrate to be imprinted for 50 s at 3500 rpm.

3.2) Bake it on a hotplate for 5 min at 120 °C.

3.3) Wait for the sample to cool down.

3.4) Spin eight drops (20 drops = 1 mL) of UV curable resist (3.9%) on the same substrate.

3.5) Place the PDMS mold (prepared in step 2) onto the sample (with both UV resist and PMMA).

3.6) Put it into a chamber with nitrogen environment.

3.7) Turn on the UV lamp to cure for 5 min.

3.8) Peel the PDMS mold off the sample and the pattern on the PDMS mold gets transferred to the sample.

4. Cr lift-off process

4.1) Reactive ion etching residual layer of UV resist and PMMA

Note: The SOP for ICP machine can be found at <https://www.nanocenter.umd.edu/equipment/fablab/sops/etch-07/Oxford%20Chlorine%20Etcher%20SOP.pdf>

4.1.1) Log in RIE ICP machine.

4.1.2) Load a blank 4-inch silicon wafer. Run the clean recipe for 10 min.

4.1.3) Take the blank silicon wafer out.

4.1.4) Mount the sample on another clean silicon wafer and load it into the machine.

4.1.5) Run the UV resist etching recipe for 2 min (the recipe can be found in Table 1).

4.1.6) Take the sample out. Load a blank 4-inch silicon wafer. Re-run the clean recipe (can be found in Table 1) for 10 min.

4.1.7) Mount the sample on a clean silicon wafer and load it into the machine.

4.1.8) Run the PMMA etching recipe (can be found in Table 1) for 2 min.

Note: Now the residual resist has been etched and substrate is exposed.

4.2) Cr e-beam evaporation

4.2.1) Log into e-beam evaporator.

4.2.2) Load the Cr metal source and sample into the chamber.

4.2.3) Set the thickness (20 nm) and deposition rate (0.03 nm/s).

4.2.4) Pump the chamber until required vacuum (10^{-7} Torr) is reached.

4.2.5) Start the deposition process.

4.2.6) Take the sample out after the deposition finishes.

4.3) Cr lift-off procedure

4.3.1) Immerse the sample in acetone with ultrasonic agitation for 5 min.

4.3.2) Clean the sample by rinsing with acetone, methanol and isopropanol.

Note: The Cr evaporated on the resist will be lifted off and a Cr mask for substrate etching is formed.

5. TiO₂ deposition

5.1) Load sample.

5.2) Set the parameters for the direct current magnetron sputtering machine

5.2.1) Use a chamber pressure of 1.5 mTorr, Ar flow of 100 SCCM and a sputtering power of 130 W.

5.2.2) Use a temperature of 27 °C and a stage rotation speed of 20 rpm.

5.3) Start the sputter process and stop at desired thickness.

5.4) Take the sample out and anneal the TiO₂ film in oxygen environment at 300 °C for 3 h.

6. High contrast grating etching

6.1) Log in the inductively coupled plasma (ICP) reactive ion etching (RIE) machine.

6.2) TiO₂ etching

6.2.1) Load a blank 4-inch silicon wafer.

6.2.2) Start and run the clean recipe (can be found in Table 1) for 10 min.

6.2.3) Unload load the blank wafer and load the sample with Cr mask.

6.2.4) Set etching time. Start TiO₂ etching recipe. The etching process will automatically stop.

6.2.6) Unload the sample.

6.3) SiO₂ etching

6.3.1) Repeat step 5.2 except use the SiO₂ etching recipe.

7. Reflectance measurement

7.1) Log in and turn on the measurement system.

7.2) Place the reflectance standard mirror on the sample holder and align the optical path.

7.3) Calibrate the system for the 100% reflectance.

7.4) Take off the reflectance standard mirror and place the HCG.

7.5) Measure the reflectance of the HCG.

7.6) Save the data and log out of the measurement system.

REPRESENTATIVE RESULTS:

Figure 1 shows the implementation of the dispersive element (multilayer high contrast grating (HCG)) in a concentrated photovoltaic system. The sun light is first reflected by the primary mirror and impinges on the reflective dispersive element, where the beam is reflected and split into different bands of different wavelengths. Each band will impinge on a certain location on the solar cell array for the best absorption and conversion to electricity. The key to this system is the design and implementation of the dispersive element, which is composed of multiple layers of HCG.

Figure 2 shows the numerical optimization result for each layer in the dispersive element. The results was calculated by the finite-difference time-domain (FDTD)⁷ based commercial simulation software “Lumerical” and further validated by rigorous coupled-wave analysis (RCWA)⁸. The refractive index of TiO₂ was from the SOPRA⁹ online database. The optimized six-layer dispersive element can provide a total reflection of more than 90% over the entire solar spectrum.^{10,11}

To demonstrate the broadband reflectance of HCG experimentally, one of the six layers in the dispersive element HCG structure is fabricated using nanoimprint fabrication. As shown in Figure 3, each grating block consists of two parts. The material of the top grating is TiO₂ and the material of the sub grating is fused silica. The pitch of the 2D HCG is 453 nm. The line width of each grating is 220 nm. The height of both top and sub grating is 340 nm. The material of the substrate is the same as the sub grating.

TiO₂ was deposited on fused silica at HP Labs using a direct current magnetron sputter machine. The chamber pressure was 1.5 mTorr with an Ar flow about 100 sccm. The sputter power was 130 W and the rate was 4 nm/min. Two batches of TiO₂ film were sputtered at different temperatures, 27 °C and 270 °C respectively. To ensure an even film deposition, substrate stage rotation was turned on (20 rpm) during sputtering. Both batches of TiO₂ films were annealed at 300 °C for 3 hours after sputtering to improve film quality. After deposition, both batches of TiO₂ films were examined using a scanning electron microscope (SEM) (Figure 4). The refractive indices of TiO₂ films were also measured (Figure 5). The measured refractive indices were 10% lower than standard database, because the film was porous which can also be observed in Figure 4. A higher sputtering temperature could increase the refractive index, however the roughness of the film was much higher. To reach a good balance between refractive indices and film roughness, the TiO₂ film which was sputtered at 27 °C was chosen as the grating material.

The major steps for nanoimprint fabrication are schematically shown in Figure 6. First, a mold with certain patterns is pressed onto the UV-curable resist on the substrate. Then UV light is applied to cure the resist. After curing, the mold can be separated from the substrate and the shape of resist is exactly the opposite of the mold. The imprinted pattern can be used as the mask to etch the residual resist, deposit metal, lift off and finally etch into the substrate. In this way, the shape of the mold gets transferred into the substrate.

To fabricate 2D HCG, a mold is duplicated from a 1D periodic grating silicon master which was fabricated by interference lithography¹². Then the same mold is used to imprint twice in orthogonal directions on the same silicon substrate to pattern a 2D hole array (Figure 7). The hybrid nanoimprint¹³ process can make large-area samples with high-resolution and little defects. The imprinted results (2D hole array silicon array) is shown in Figure 8. The roughness of edges can be further reduced with the help of edge smoothing technologies¹⁴.

After nanoimprint patterning and Cr mask array is completed, an ICP RIE machine is used to etch the sample. Two different etching recipes were developed for TiO₂ and fused silica respectively, which is shown in table 1. The fabricated structure is shown in Figure 9.

The reflectance (from the normal incidence) of 2D HCG was measured using two different spectrometers with different types of detectors, the normal detector and the sphere integration detector. In contrast to sphere integration detector, the normal detector has a relatively small angle of acceptance and therefore will not receive the scattered light. As shown in Figure 10, the difference in reflectance curves measured by both detectors indicates that the light is scattered by the HCG due to the structure roughness. The difference between integration sphere measurement and simulation data is mainly due to the loss of material and fabrication errors. The reflectance curves can demonstrate that the fabricated device can work as a band reflector as one layer in the dispersive element. Due to the high contrast of index between the grating and the substrate, HCG has good angle independence. The reflectance curve will not change much when the incidence angle is less than 15°.

Figure 1: The implementation of the dispersive element (multiplayer HCG) in a concentrated photovoltaic (CPV) system

Figure 2: Numerically optimized reflectance curves for the dispersive element design (six-layer stacked HCG) that can cover most of the solar spectrum

Figure 3: The optimized structure of a HCG for demonstration of nanoimprint fabrication

Figure 4: The SEM images (cross-sectional view) of sputtered TiO₂ films at (a) 27 °C and (b) 270 °C

Figure 5: Measured and standard refractive (SOPRA database) indices of sputtered TiO₂ films

Figure 6: Nanoimprint fabrication process

Figure 7: The SEM image of 2D hole array silicon master (top-down view)

Figure 8: The photo of 2D hole array silicon master fabricated by PDMS-based nanoimprint

Figure 9: The SEM image (cross-sectional view) of the fabricated 2D HCG

Figure 10: One simulated reflectance curve and two measured reflectance curves using sphere integration detector and normal detector respectively

Figure 11: (a) Effect of refractive index on HCG reflectance; (b) Effect of sidewall angle on HCG reflectance

Table 1: The table of etching recipes for TiO_2 , fused silica, UV resist, PMMA and clean.

DISCUSSION:

First, the quality of the TiO_2 film is very crucial for the HCG performance. The reflectance peak will be higher if the TiO_2 film has less loss and surface roughness. The TiO_2 film with a higher refractive index is also favorable because the optical mode confinement will be enhanced by a higher contrast in index, which can give rise to a flatter and broader reflectance band in HCG.

Second, the fabrication errors will have significant effects on the HCG and should be avoided. The roughness introduced in fabrication will cause more light to be scattered, so the reflectance will become lower. The deviation of parameters in HCG fabrication including line width, height and pitch will not allow the device to work optimally as in simulation. Moreover, the reflectance of HCG strongly depends on the etching profile, i.e. the angle of sidewall. In Figure 11, the effect of sidewall angles on the reflectance of HCG is numerically calculated. As the sidewall angles decrease from 90° to 84° , the average reflectance drops from over 90% to less than 50%, because the HCG behaves more like a cone-shaped anti-reflection coating when the sidewall angle is small.

The optical efficiency of the dispersive element is important for the overall efficiency of the CPV system, so the reflectance of each layer of HCG should be as high as possible. Based on the discussion above, while the optical efficiency for the fabricated layer is about 60%, there are several possible improvements for a better HCG reflectance. The TiO_2 sputtering condition can be further optimized to generate the film with a higher index, less surface roughness and lower optical loss. The dry etching recipes should be further adjusted for a better etching profile, making the grating straighter, which can be achieved by adjusting the combination of gases (C_4F_8 , SF_6 and O_2) to balance the etching and re-deposition process. The nanoimprint and lift-off process should be improved to avoid roughness and fabrication errors so that the unnecessary scattering can be reduced to increase the overall optical efficiency.

By stacking multiple layers of two-dimensional HCGs with different pitches, the dispersive mirror can operate in much broader spectrum. The mirror can reflectively direct light into

different angles according to wavelengths, in a way of packaging all HCG layers subsequently in different tilting angles. Moreover, the dispersive mirror can be fabricated using nanoimprint lithography (NIL) in a large area and at a low cost. Moreover, the proposed system features an easy integration with existing concentrator photovoltaic (CPV) setup so it has the potential to be accepted widely by the industry to improve solar energy conversion efficiency.

DISCLOSURES:

The authors have nothing to disclose.

ACKNOWLEDGMENTS:

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Figure1
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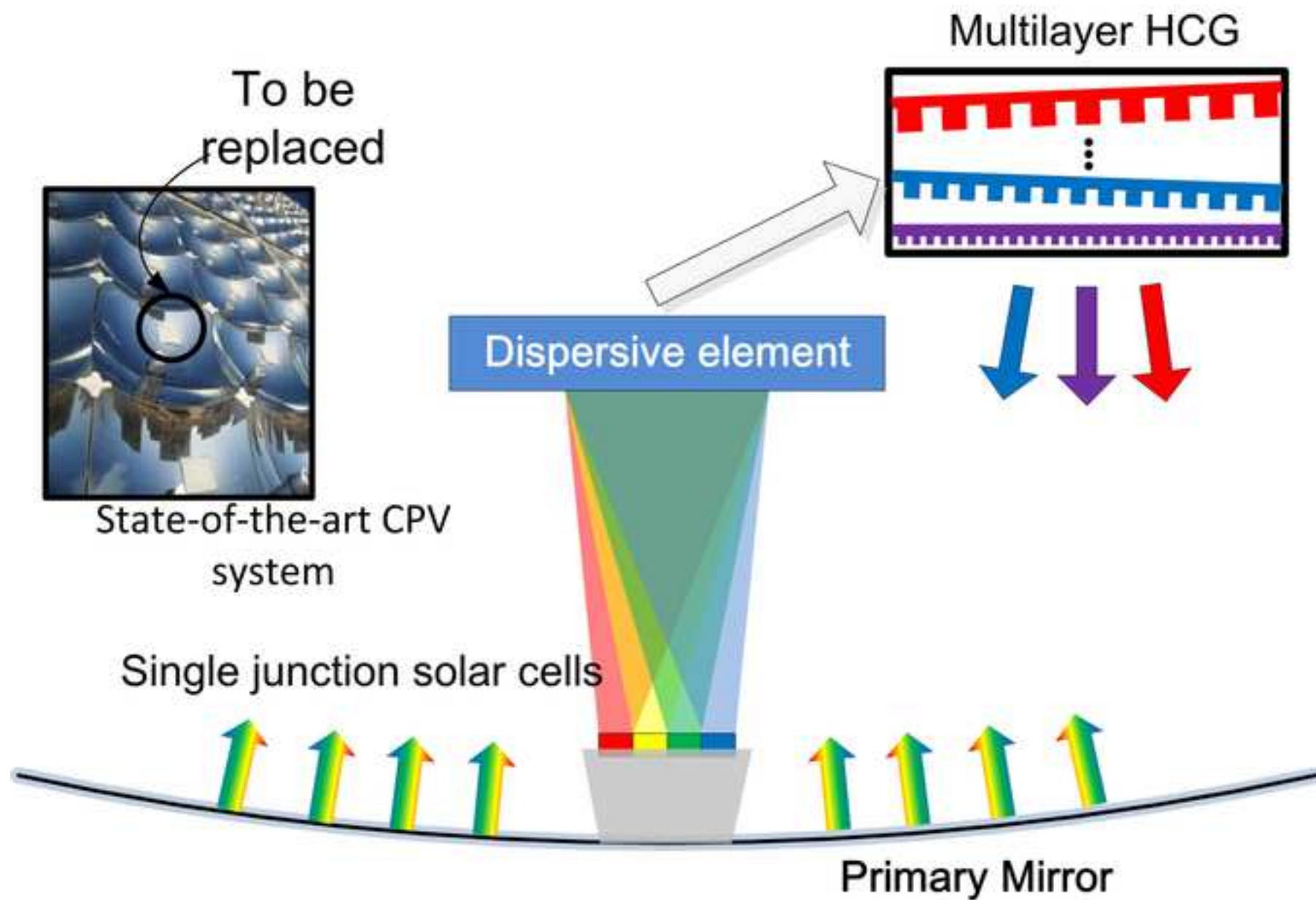


Figure2

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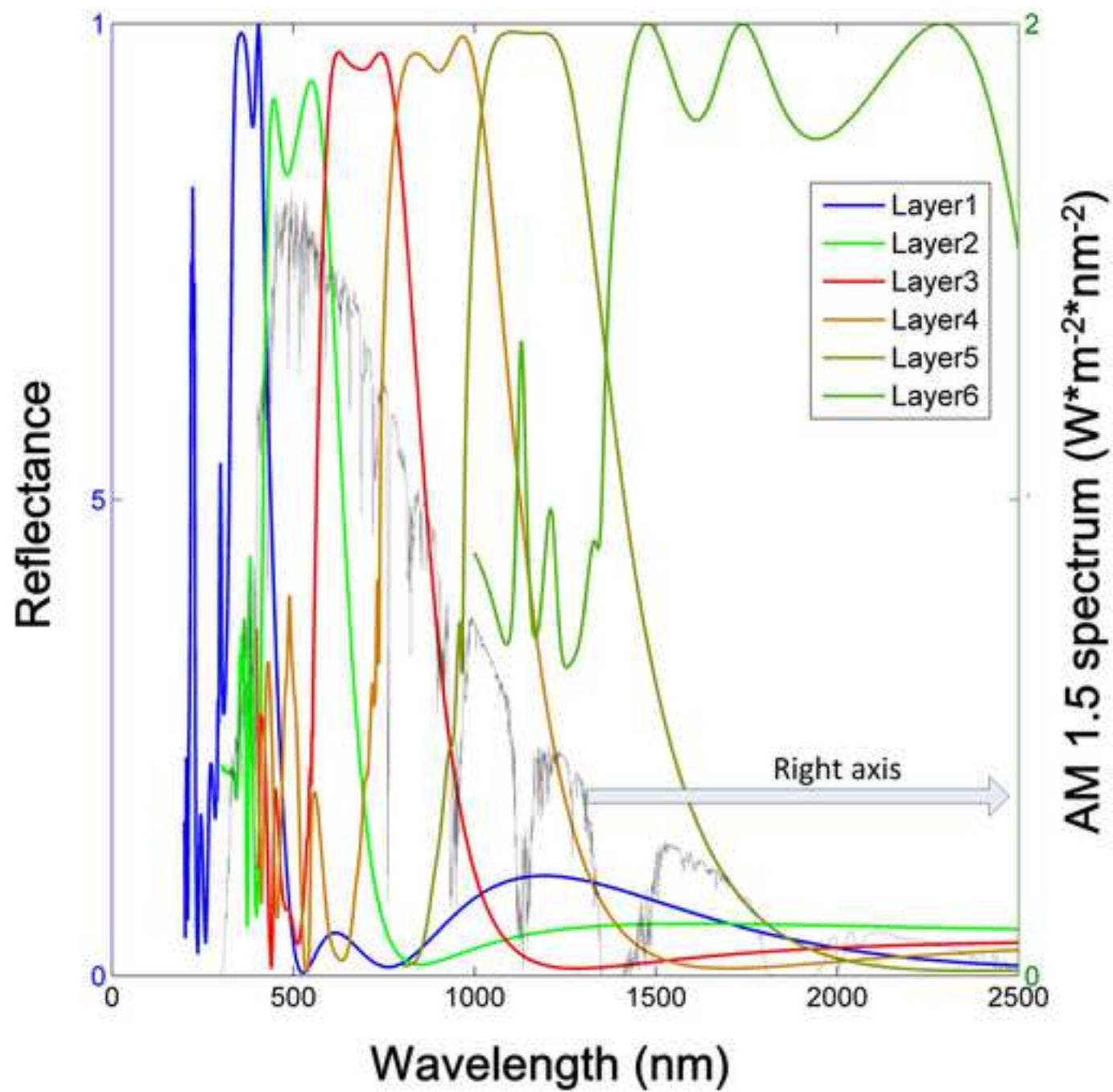


Figure3

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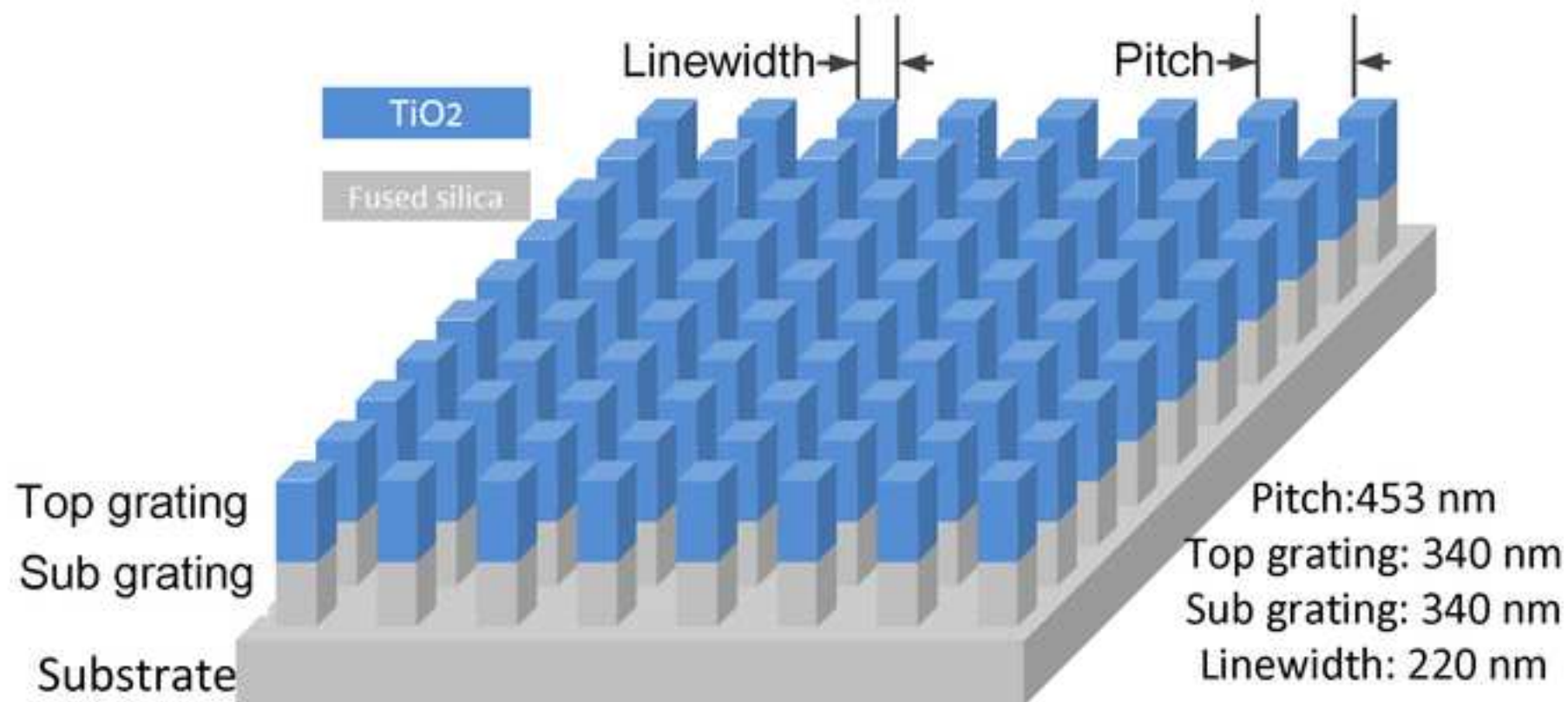


Figure4

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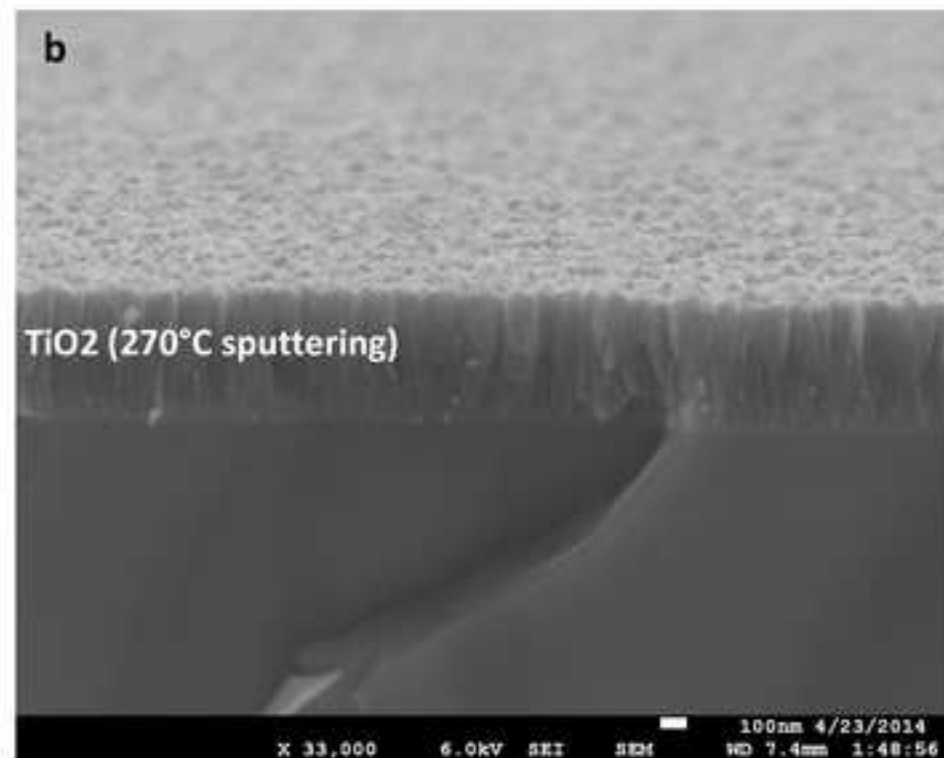
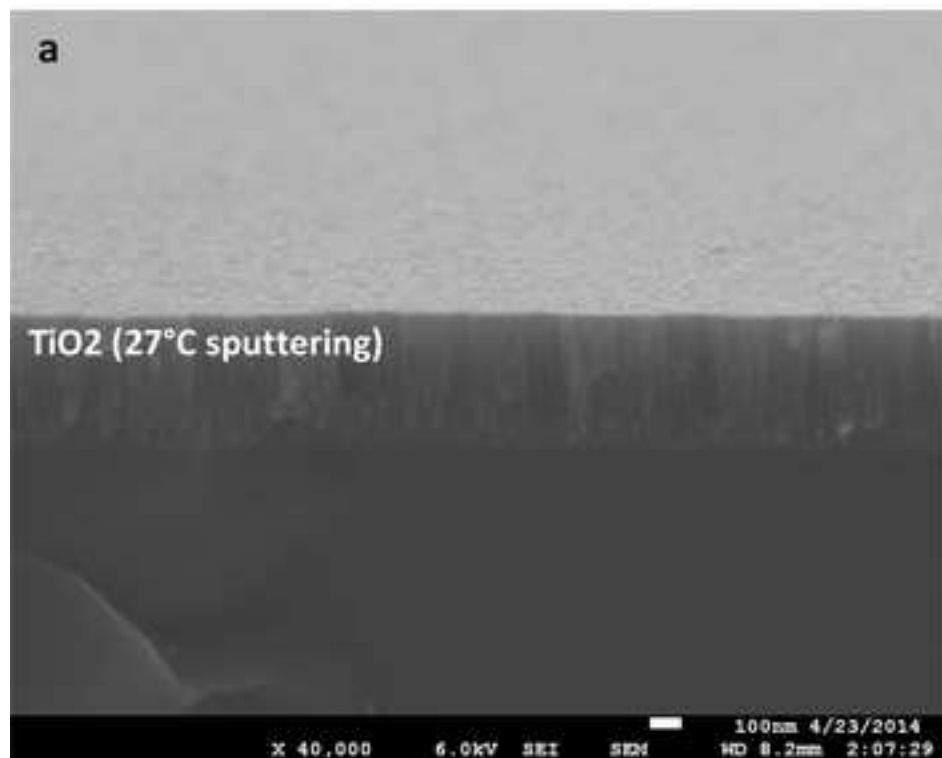


Figure5
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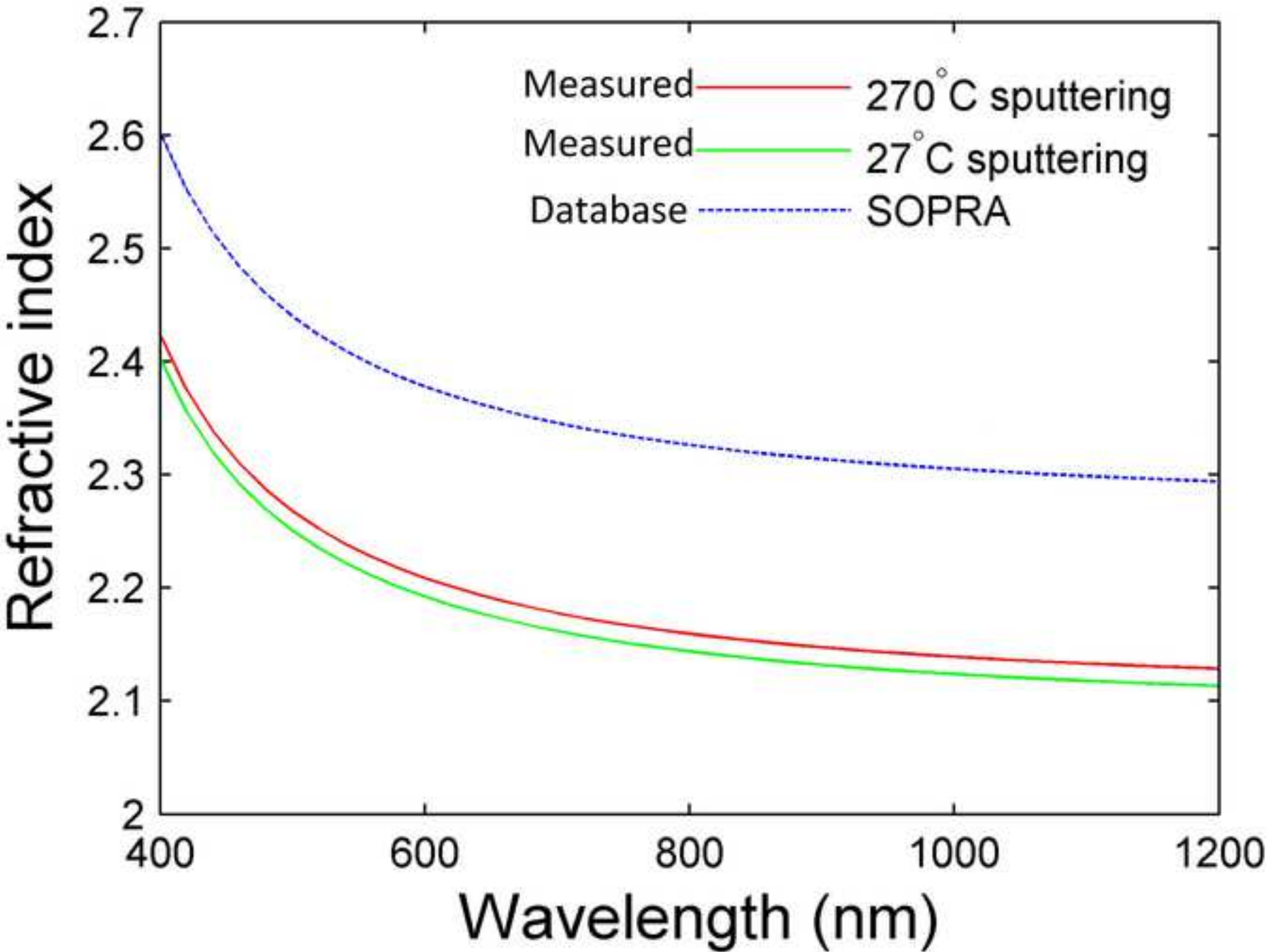


Figure6

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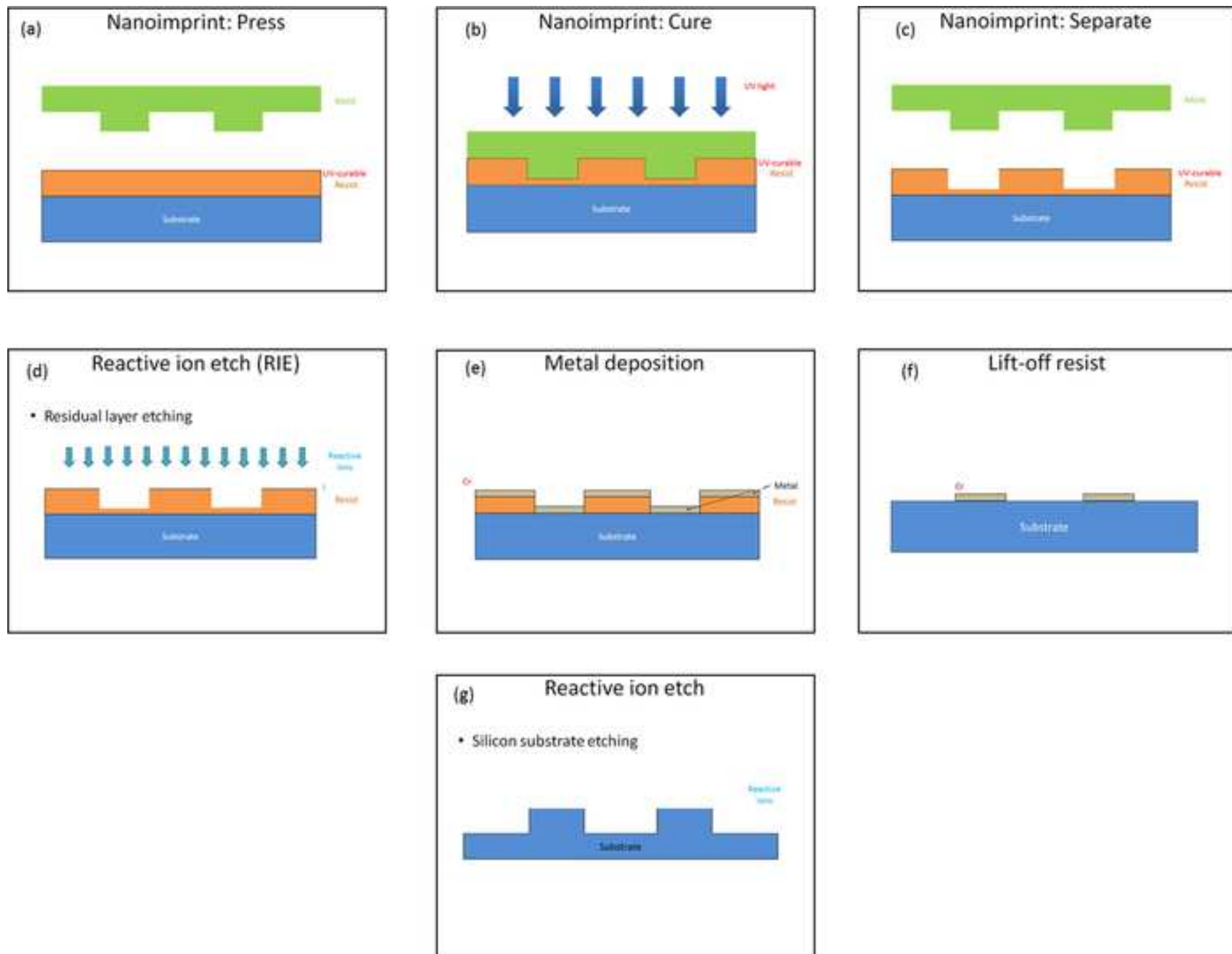


Figure 7

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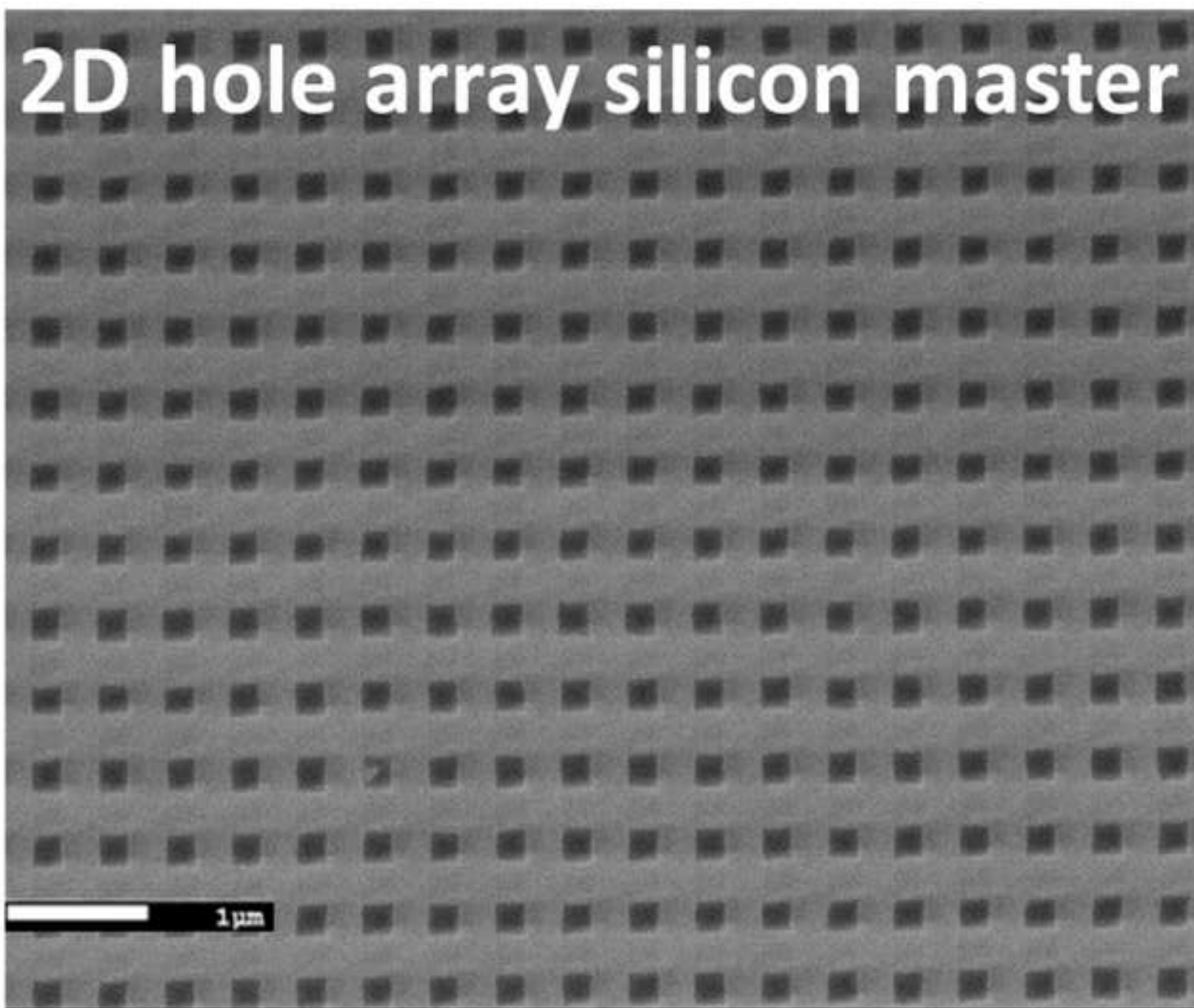


Figure8

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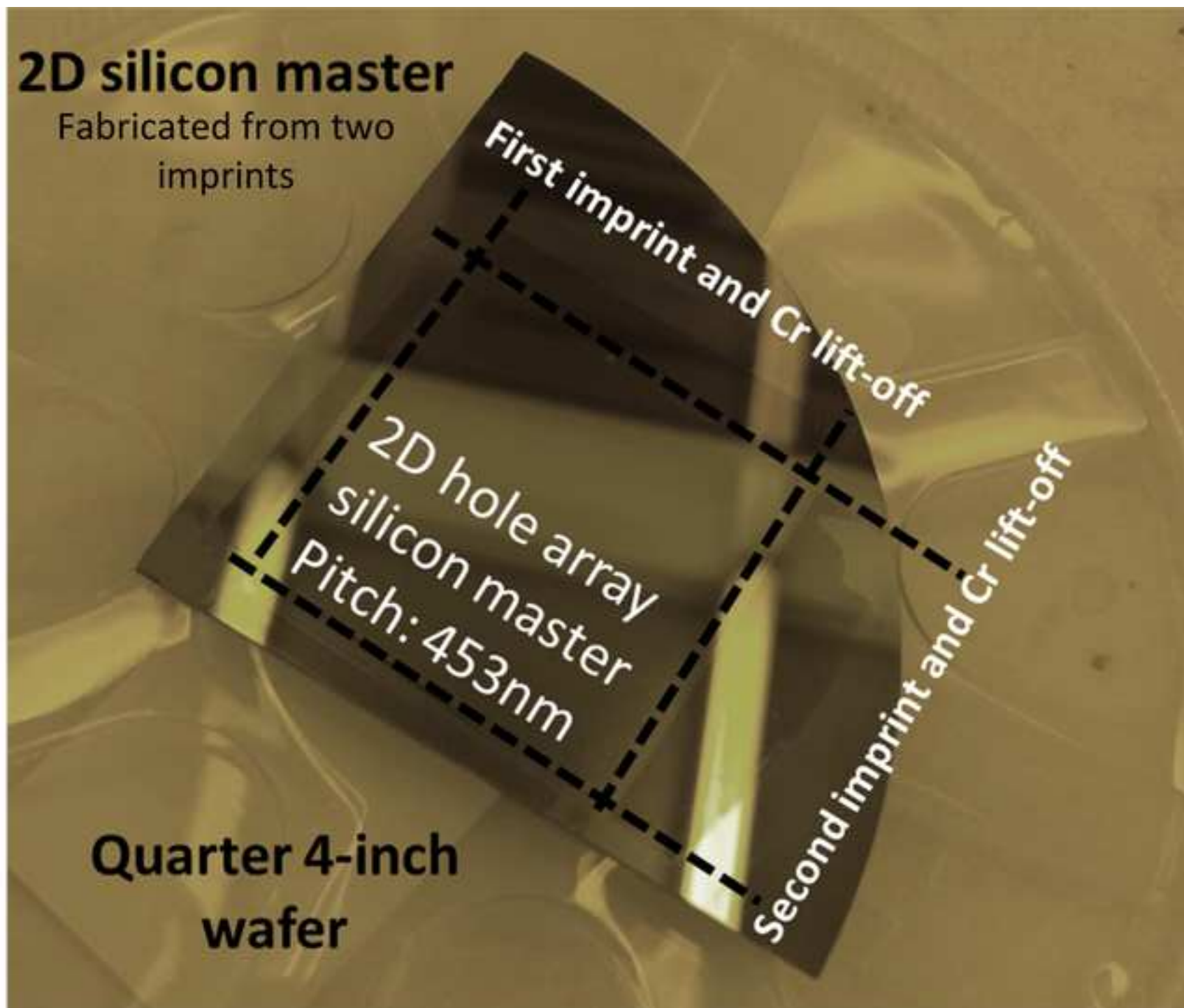


Figure9

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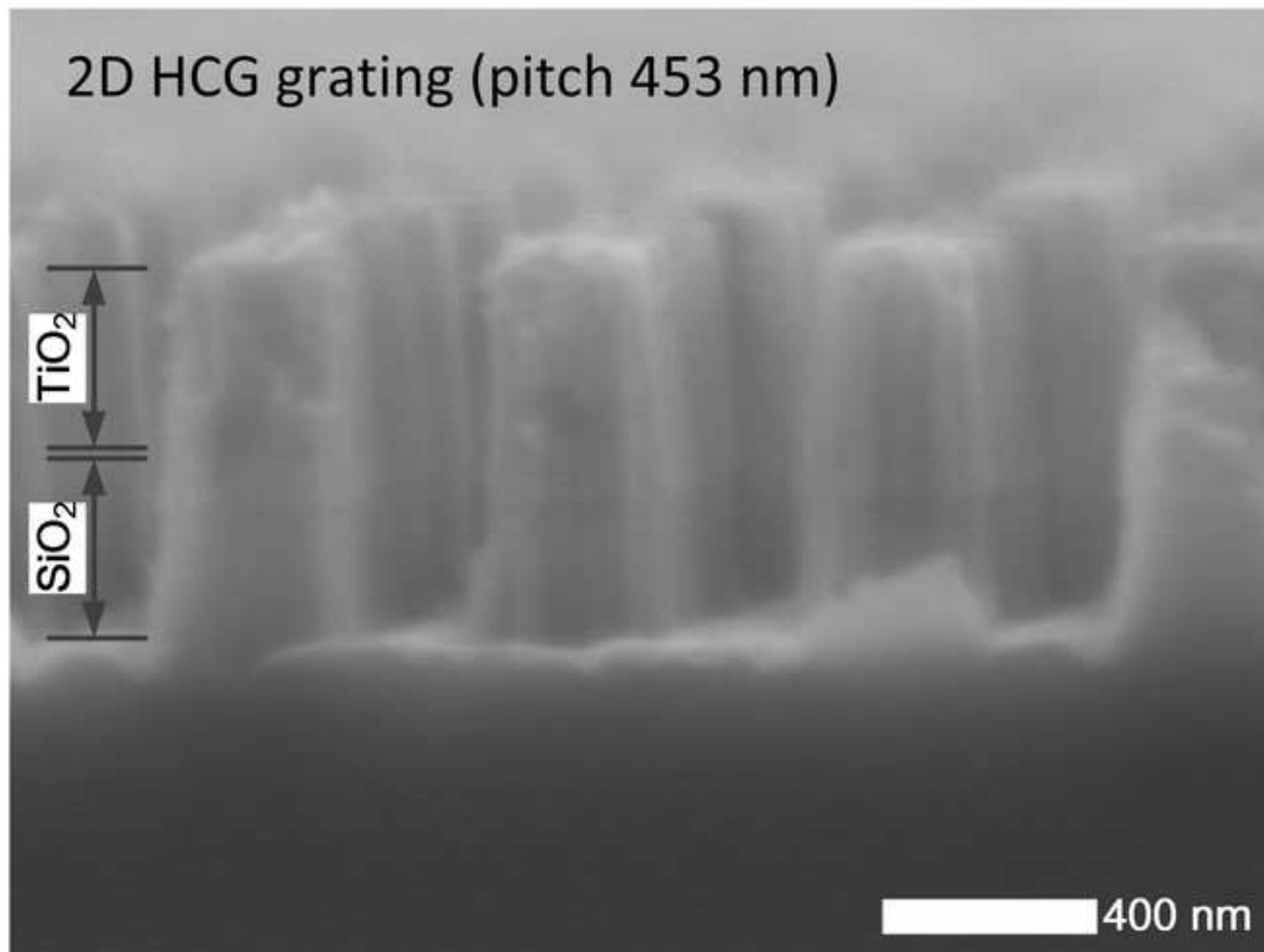


Figure10
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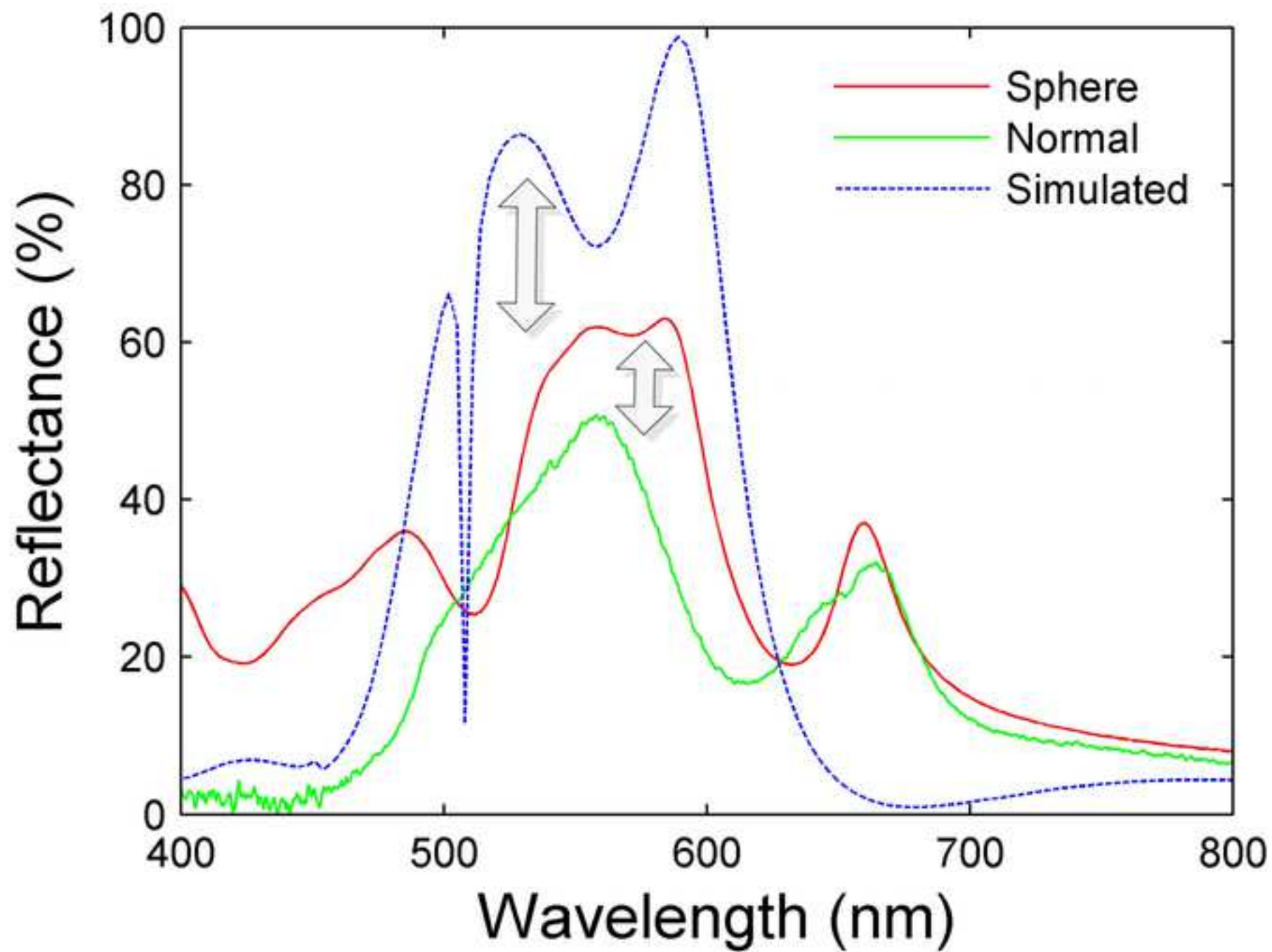
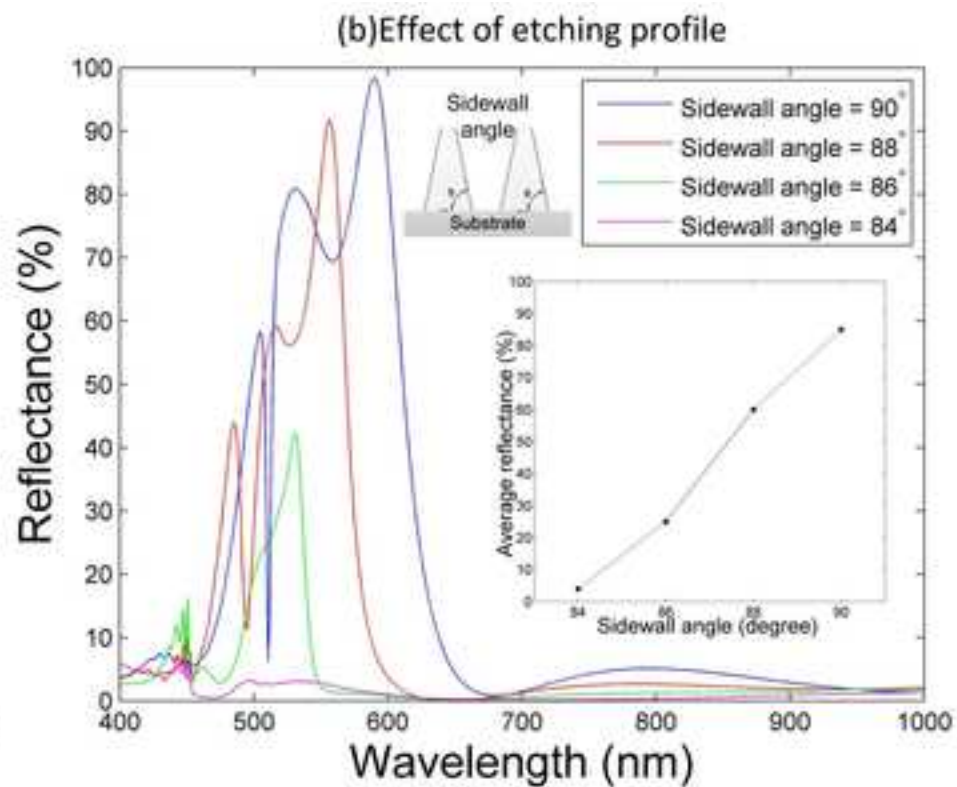
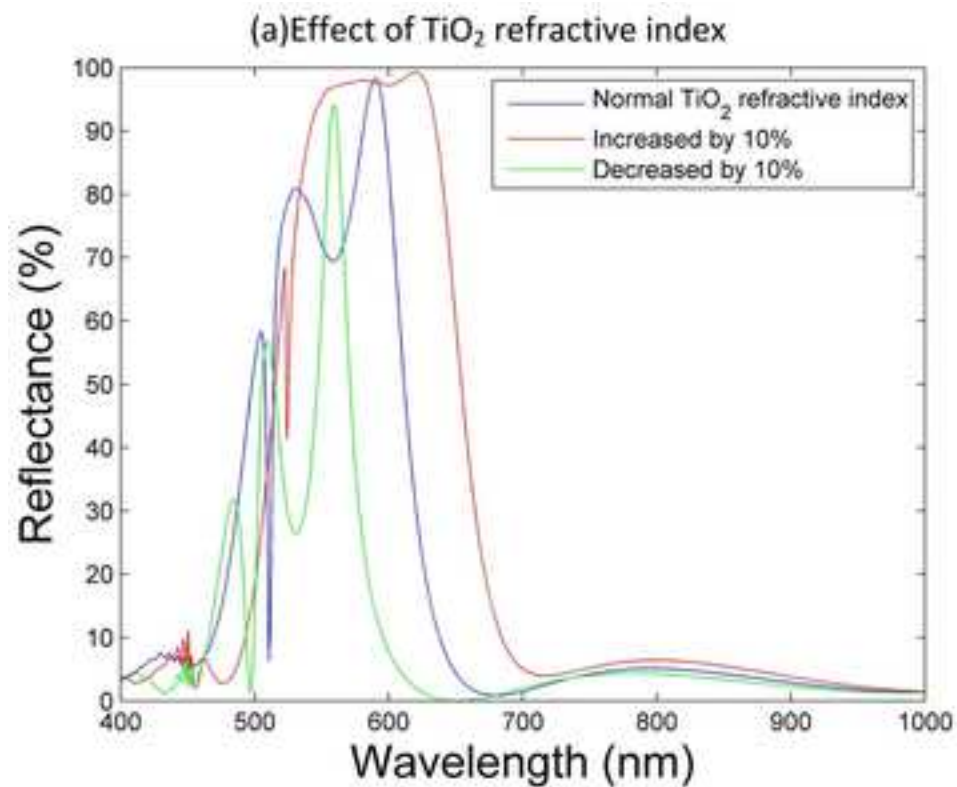


Figure11
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Name of Material/ Equipment	Company	Catalog Number
184 SILICONE ELASTOMER KIT	SYLGARD	
4-inch silicon wafer	Universitywafer	
4-inch fused silica wafer	Universitywafer	
Poly(methyl methacrylate)	SIGMA-ALDRICH	182265
UV-curable resist		
PlasmaLab System 100	Oxford Instruments	
UV curing system for nanoimprint fabrication		
Ocean Optics HR-4000	Ocean Optics	HR-4000
Lambda 950 UV / VIS	PerkinElmer	
JSM-7001F-LV	JEOL	
DC magnetron sputtering machine		
Metal e-beam evaporator	Temescal	BJD-1800

Comments/Description

Polydimethylsiloxane (PDMS)

Nor available on market

ICP IRE machine

Not available on market

Spectrometer with normal detector

spectrometer with hemisphere intergration detector

Field emission SEM

Equipment is in HP labs, who helped us to sputter the TiO₂

Table 1 in excel
[Click here to download Excel Spreadsheet- Table of Materials/Equipment: Table1.xlsx](#)

	ICP Power	Forward Power	SF6 Flow	C4F8 Flow	O2 Flow	Pressure	Etching Rate
TiO2	0 W	25 W	25 sccm	10 sccm	10 sccm	10mTorr	43nm/min
Fused silica	0 W	100 W	0 sccm	15 sccm	15 sccm	10mTorr	20nm/min
Resist	0 W	25 W	25 sccm	15 sccm	0	10mTorr	22nm/min
PMMA	0W	30W	0	0	30 sccm	2mTorr	55nm/min
Clean	1000W	200W	0	0	50 sccm	50mTorr	NA



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Fabrication of high contrast gratings for the spectrum splitting dispersive element in a concentrated photovoltaic system

Author(s):

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1 **TITLE:**

2 **Fabrication of high contrast gratings for the spectrum splitting dispersive element in a**
3 **concentrated photovoltaic system**

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27 **KEYWORDS:**

28 Parallel spectrum splitting, dispersive element, high contrast grating, concentrated photovoltaic
29 system, nanoimprint lithography, reactive ion etching

30
31 **SHORT ABSTRACT:**

32 The fabrication of high contrast gratings as the parallel spectrum splitting dispersive element in
33 a concentrated photovoltaic system is demonstrated. Fabrication processes including
34 nanoimprint lithography, TiO₂ sputtering and reactive ion dry etching are described.
35 Reflectance measurement results are used to characterize the optical performance.

36
37 **LONG ABSTRACT:**

38 High contrast gratings are designed and fabricated and its application is proposed in a parallel
39 spectrum splitting dispersive element that can improve the solar conversion efficiency of a
40 concentrated photovoltaic system. The proposed system will also lower the solar cell cost in the
41 concentrated photovoltaic system by replacing the expensive tandem solar cells with the cost-
42 effective single junction solar cells. The structures and the parameters of high contrast gratings
43 for the dispersive elements were numerically optimized. The large-area fabrication of high

contrast gratings was experimentally demonstrated using nanoimprint lithography and dry etching. The quality of grating material and the performance of the fabricated device were both experimentally characterized. By analyzing the measurement results, the possible side effects from the fabrication processes are discussed and several methods that have the potential to improve the fabrication processes are proposed, which can help to increase the optical efficiency of the fabricated devices.

INTRODUCTION:

Our modern society will not survive without moving a significant portion of energy consumption to renewable energy sources. To make this happen, we have to find a way to harvest renewable energy at a cost lower than petroleum-based energy sources in the near future. Solar energy is the most abundant renewable energy on earth. Despite that a lot of progresses have been made in solar energy harvesting, it is still very challenging to compete with petroleum-based energy sources. Improving the efficiency of solar cells is one of the most efficient ways to lower the system cost of solar energy harvesting.

Optical lenses and dish reflectors are usually used in most concentrated photovoltaic (CPV) systems⁴¹ to achieve a high concentration of solar power incidence on the small-area solar cells, so it is economically viable to exploit expensive tandem multi-junction solar cells⁴² in CPV systems, and to maintain a reasonable cost at the same time. However, for most non-concentrated photovoltaic systems, which usually require a large-area installment of solar cells, the high-cost tandem solar cells cannot be incorporated, although they usually have a broader solar spectrum response and a higher overall conversion efficiency than the single junction solar cells⁴³.

Recently, with the help of the parallel spectrum splitting optics (i.e. dispersive element), the parallel spectrum splitting photovoltaic technology⁴⁴ has made it possible that a similar or better spectrum coverage and conversion efficiency can be achieved without using the expensive tandem solar cells. The solar spectrum can be split into different bands and each band can be absorbed and converted to electricity by the specialized single-junction solar cells. In this way, the expensive tandem solar cells in CPV systems can be replaced by a parallel distribution of single-junction solar cells without any compromise on the performance.

The dispersive element that was designed in this report can be applied in a reflective CPV system (which is based on dish reflectors) to realize parallel spectrum splitting for the improved solar-electricity conversion efficiency and reduced cost. ~~Multilayer high contrast gratings (HCG)~~⁵ Multilayer high contrast gratings (HCG)⁵ is used as the dispersive element by designing each layer of HCG to work as an optical band reflector. The structures and parameters of the dispersive element are numerically optimized. Moreover, the fabrication of high contrast gratings for the dispersive element by using dielectric (TiO₂) sputtering, nanoimprint lithography⁶⁶ and reactive ion etching is studied and demonstrated.

PROTOCOL:

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88 **1. Prepare the blank Polydimethylsiloxane (PDMS) substrate for nanoimprint mold**
89
90 1.1) Silicon wafer treatment process
91
92 1.1.1) Clean a 4-inch silicon wafer by rinsing with acetone, methanol and isopropanol.
93
94 1.1.2) Blow it dry using the nitrogen gun.
95
96 1.1.3) Clean it using piranha solution (3:1 mixture of sulfuric acid with 30% hydrogen peroxide)
97 by soaking inside for 15 min.
98
99 1.1.4) Rinse it with DI water. Blow dry using the nitrogen gun.
100
101 | 1.1.5) Place the wafer in a glass desiccator. Add a drop (20 drops = 1 mL) of releasing agent
102 (Trichlorosilane) into the desiccator.
103
104 | 1.1.6) Pump down the desiccator until the gauge reads -30 inHg and wait for 5 hr.
105
106 1.1.7) Take the wafer out, which has been treated with releasing agent.
107
108 **1.2) Preparation of PDMS film (used as mold in nanoimprint)**
109
110 **1.2.1) Weigh 10 g of silicone elastomer base and 1 g of curing agent.**
111
112 **1.2.2) Add them in the same glass beaker.**
113
114 **1.2.3) Stir and mix with a glass rod for 5 min.**
115
116 | **1.2.4) Put the mixture into a vacuum desiccator until the gauge reads -30 inHg to pump out all**
117 **the trapped air bubbles.**
118
119 **1.2.5) Spread them evenly onto the treated 4-inch silicon wafer.**
120
121 **1.2.6) Bake the wafer with PDMS on top in the vacuum oven for 7 hours at 80 °C to cure the**
122 **PDMS film.**
123
124 **2. Prepare the nanoimprint mold (duplication from the master mold)**
125
126 | **2.1) Spin twelve drops (20 drops = 1 mL) of UV curable resist (15.2%) on a clean blank silicon**
127 **wafer for 30 s at 1500 rpm.**
128
129 **2.2) Carefully peel a piece of PDMS film off the treated silicon wafer.**
130
131 **2.3) Put the PDMS film onto the UV curable resist and let it absorb the UV resist for 5 min then**

132 peel it off.

133
134 2.4) Repeat 2.1 - 2.3 on the same PDMS film for two times. Absorb the UV resist for 3 min and 1
135 min respectively.

136
137 2.5) Place the PDMS film (after three-time UV resist absorption) onto a silicon master mold.

138
139 2.6) Put it into a chamber with nitrogen environment.

140
141 2.7) Turn on UV lamp to cure the sample for 5 min.

142
143 2.8) Peel off the PDMS film. The cured UV resist on the PDMS will keep the negative pattern of
144 the master mold.

145
146 2.9) Use RF O₂ plasma to treat the PDMS mold. (RF power: 30 W, pressure: 260 mTorr, time: 1
147 min)

148
149 2.10) Place the PDMS mold in a vacuum chamber with one drop (20 drops = 1 mL) of releasing
150 agent for 2 hr.

151
152 **3. Nanoimprint pattern transfer**

153
154 3.1) Spin eight drops (20 drops = 1 mL) of PMMA (996k, 3.1%) on the substrate to be imprinted
155 for 50 s at 3500 rpm.

156
157 3.2) Bake it on a hotplate for 5 min at 120 °C.

158
159 3.3) Wait for the sample to cool down.

160
161 3.4) Spin eight drops (20 drops = 1 mL) of UV curable resist (3.9%) on the same substrate.

162
163 3.5) Place the PDMS mold (prepared in step 2) onto the sample (with both UV resist and
164 PMMA).

165
166 3.6) Put it into a chamber with nitrogen environment.

167
168 3.7) Turn on the UV lamp to cure for 5 min.

169
170 3.8) Peel the PDMS mold off the sample and the pattern on the PDMS mold gets transferred to
171 the sample.

172
173 **4. Cr lift-off process**

174
175 4.1) Reactive ion etching residual layer of UV resist and PMMA

176
177 Note: The SOP for ICP machine can be found at
178 [https://www.nanocenter.umd.edu/equipment/fablab/sops/etch-](https://www.nanocenter.umd.edu/equipment/fablab/sops/etch-07/Oxford%20Chlorine%20Etcher%20SOP.pdf)
179 [07/Oxford%20Chlorine%20Etcher%20SOP.pdf](https://www.nanocenter.umd.edu/equipment/fablab/sops/etch-07/Oxford%20Chlorine%20Etcher%20SOP.pdf)
180
181 4.1.1) Log in RIE ICP machine.
182
183 4.1.2) Load a blank 4-inch silicon wafer. Run the clean recipe for 10 min.
184
185 4.1.3) Take the blank silicon wafer out.
186
187 4.1.4) Mount the sample on another clean silicon wafer and load it into the machine.
188
189 4.1.5) Run the UV resist etching recipe for 2 min (the recipe can be found in Table 1).
190
191 4.1.6) Take the sample out. Load a blank 4-inch silicon wafer. Re-run the clean recipe (can be
192 found in Table 1) for 10 min.
193
194 4.1.7) Mount the sample on a clean silicon wafer and load it into the machine.
195
196 4.1.8) Run the PMMA etching recipe (can be found in Table 1) for 2 min.
197
198 Note: Now the residual resist has been etched and substrate is exposed.
199
200 4.2) Cr e-beam evaporation
201
202 4.2.1) Log into e-beam evaporator.
203
204 4.2.2) Load the Cr metal source and sample into the chamber.
205
206 4.2.3) Set the thickness (20 nm) and deposition rate (0.03 nm/sec).
207
208 4.2.4) Pump the chamber until required vacuum (10^{-7} Torr) is reached.
209
210 4.2.5) Start the deposition process.
211
212 4.2.6) Take the sample out after the deposition finishes.
213
214 4.3) Cr lift-off procedure
215
216 4.3.1) Immerse the sample in acetone with ultrasonic agitation for 5 min.
217
218 4.3.2) Clean the sample by rinsing with acetone, methanol and isopropanol.
219

220 Note: The Cr evaporated on the resist will be lifted off and a Cr mask for substrate etching is
221 formed.

222
223 | **5. ~~High contrast grating etching~~ TiO₂ deposition**

224
225 | 5.1) Load sample

226
227 | 5.2) Set the parameters for the direct current magnetron sputtering machine

228
229 | 5.1.1) Chamber pressure: 1.5 mTorr, Ar flow: 100 SCCM, Sputtering power: 130 W

230
231 | 5.1.2) Temperature: 27 °C, Stage rotation speed: 20 rpm

232
233 | 5.3) Start the sputter process and stop at desired thickness

234
235 | 5.4) Take the sample out and anneal the TiO₂ film in oxygen environment at 300 °C for 3 hr.

236
237 | **6. High contrast grating etching**

238
239 | 6.1) Log in the inductively coupled plasma (ICP) reactive ion etching (RIE) machine.

240
241 | 6.2) TiO₂ etching

242
243 | 6.2.1) Load a blank 4-inch silicon wafer.

244
245 | 6.2.2) Start and run the clean recipe (can be found in Table 1) for 10 min.

246
247 | 6.2.3) Unload load the blank wafer and load the sample with Cr mask.

248
249 | 6.2.4) Set etching time. Start TiO₂ etching recipe. The etching process will automatically stop.

250
251 | 6.2.6) Unload the sample.

252
253 | 6.3) SiO₂ etching

254
255 | 6.3.1) Repeat the step 5.2 except use the SiO₂ etching recipe.

256
257 | **6.7. Reflectance measurement**

258
259 | 6.7.1) Log in and turn on the measurement system.

260
261 | 6.7.2) Place the reflectance standard mirror on the sample holder and align the optical path.

262
263 | 6.7.3) Calibrate the system for the 100% reflectance.

264
265 | 6Z.4) Take off the reflectance standard mirror and place the HCG.

266
267 | 6Z.5) Measure the reflectance of the HCG.

268
269 | 6Z.6) Save the data and log out of the measurement system.

270
271 **REPRESENTATIVE RESULTS:**

272 Figure 1 shows the implementation of the dispersive element (multilayer high contrast grating
273 (HCG)) in a concentrated photovoltaic system. The sun light is first reflected by the primary
274 mirror and impinges on the reflective dispersive element, where the beam is reflected and split
275 into different bands of different wavelengths. Each band will impinge on a certain location on
276 the solar cell array for the best absorption and conversion to electricity. The key to this system
277 is the design and implementation of the dispersive element, which is composed of multiple
278 layers of HCG.

279
280 Figure 2 shows the numerical optimization result for each layer in the dispersive element. ~~The~~
281 ~~results was calculated by the finite-difference time-domain (FDTD)⁷-based commercial~~
282 ~~simulation software “Lumerical” and further validated by rigorous coupled-wave analysis~~
283 ~~(RCWA)⁸. The refractive index of TiO₂ was from the SOPRA⁹ online database. The optimized six-~~
284 ~~layer dispersive element can provide a total reflection of more than 90% over the entire solar~~
285 ~~spectrum.^{10,11}~~ The results was calculated by the finite-difference time-domain (FDTD)⁷ based
286 commercial simulation software “Lumerical” and further validated by rigorous coupled-wave
287 analysis (RCWA)⁸. The refractive index of TiO₂ was from the SOPRA⁹ online database. The
288 optimized six-layer dispersive element can provide a total reflection of more than 90% over the
289 entire solar spectrum.^{10,11}

290
291 To demonstrate the broadband reflectance of HCG experimentally, one of the six layers in the
292 dispersive element HCG structure is fabricated using nanoimprint fabrication. As shown in
293 Figure 3, each grating block consists of two parts. The material of the top grating is TiO₂ and the
294 material of the sub grating is fused silica. The pitch of the 2D HCG is 453 nm. The line width of
295 each grating is 220 nm. The height of both top and sub grating is 340 nm. The material of the
296 substrate is the same as the sub grating.

297
298 TiO₂ was deposited on fused silica at HP Labs using a direct current magnetron sputter machine.
299 The chamber pressure was 1.5 mTorr with an Ar flow about 100 sccm. The sputter power was
300 130 W and the rate was 4 nm/min. Two batches of TiO₂ film were sputtered at different
301 temperatures, 27 °C and 270 °C respectively. To ensure an even film deposition, substrate stage
302 rotation was turned on (20 rpm) during sputtering. Both batches of TiO₂ films were annealed at
303 300 °C for 3 hours after sputtering to improve film quality. After deposition, both batches of
304 TiO₂ films were examined using a scanning electron microscope (SEM) (Figure 4). The refractive
305 indices of TiO₂ films were also measured (Figure 5). The measured refractive indices were 10%
306 lower than standard database, because the film was porous which can also be observed in
307 Figure 4. A higher sputtering temperature could increase the refractive index, however the

roughness of the film was much higher. To reach a good balance between refractive indices and film roughness, the TiO₂ film which was sputtered at 27 °C was chosen as the grating material.

The major steps for nanoimprint fabrication are schematically shown in Figure 6. First, a mold with certain patterns is pressed onto the UV-curable resist on the substrate. Then UV light is applied to cure the resist. After curing, the mold can be separated from the substrate and the shape of resist is exactly the opposite of the mold. The imprinted pattern can be used as the mask to etch the residual resist, deposit metal, lift off and finally etch into the substrate. In this way, the shape of the mold gets transferred into the substrate.

~~To fabricate 2D HCG, a mold is duplicated from a 1D periodic grating silicon master which was fabricated by interference lithography¹². Then the same mold is used to imprint twice in orthogonal directions on the same silicon substrate to pattern a 2D hole array (Figure 7). The hybrid nanoimprint¹³ process can make large-area samples with high-resolution and little defects. The imprinted results (2D hole array silicon array) is shown in Figure 8.~~

To fabricate 2D HCG, a mold is duplicated from a 1D periodic grating silicon master which was fabricated by interference lithography¹². Then the same mold is used to imprint twice in orthogonal directions on the same silicon substrate to pattern a 2D hole array (Figure 7). The hybrid nanoimprint¹³ process can make large-area samples with high-resolution and little defects. The imprinted results (2D hole array silicon array) is shown in Figure 8. The roughness of edges can be further reduced with the help of edge smoothing technologies¹⁴.

After nanoimprint patterning and Cr mask array is completed, an ICP RIE machine is used to etch the sample. Two different etching recipes were developed for TiO₂ and fused silica respectively, which is shown in table 1. The fabricated structure is shown in Figure 9.

The reflectance (from the normal incidence) of 2D HCG was measured using two different spectrometers with different types of detectors, the normal detector and the sphere integration detector. In contrast to sphere integration detector, the normal detector has a relatively small angle of acceptance and therefore will not receive the scattered light. As shown in Figure 10, the difference in reflectance curves measured by both detectors indicates that the light is scattered by the HCG due to the structure roughness. The difference between integration sphere measurement and simulation data is mainly due to the loss of material and fabrication errors. The reflectance curves can demonstrate that the fabricated device can work as a band reflector as one layer in the dispersive element. Due to the high contrast of index between the grating and the substrate, HCG has good angle independence. The reflectance curve will not change much when the incidence angle is less than 15°.

Figure 1: The implementation of the dispersive element (multiplayer HCG) in a concentrated photovoltaic (CPV) system

Figure 2: Numerically optimized reflectance curves for the dispersive element design (six-layer stacked HCG) that can cover most of the solar spectrum

Figure 3: The optimized structure of a HCG for demonstration of nanoimprint fabrication

Figure 4: The SEM images (cross-sectional view) of sputtered TiO_2 films at (a) 27 °C and (b) 270 °C

Figure 5: Measured and standard refractive (SOPRA database) indices of sputtered TiO_2 films

Figure 6: Nanoimprint fabrication process

Figure 7: The SEM image of 2D hole array silicon master (top-down view)

Figure 8: The photo of 2D hole array silicon master fabricated by PDMS-based nanoimprint

Figure 9: The SEM image (cross-sectional view) of the fabricated 2D HCG

Figure 10: One simulated reflectance curve and two measured reflectance curves using sphere integration detector and normal detector respectively

Figure 11: (a) Effect of refractive index on HCG reflectance; (b) Effect of sidewall angle on HCG reflectance

Table 1: The table of etching recipes for TiO_2 , fused silica, UV resist, PMMA and clean.

DISCUSSION:

First, the quality of the TiO_2 film is very crucial for the HCG performance. The reflectance peak will be higher if the TiO_2 film has less loss and surface roughness. The TiO_2 film with a higher refractive index is also favorable because the optical mode confinement will be enhanced by a higher contrast in index, which can give rise to a flatter and broader reflectance band in HCG.

Second, the fabrication errors will have significant effects on the HCG and should be avoided. The roughness introduced in fabrication will cause more light to be scattered, so the reflectance will become lower. The deviation of parameters in HCG fabrication including line width, height and pitch will not allow the device to work optimally as in simulation. Moreover, the reflectance of HCG strongly depends on the etching profile, i.e. the angle of sidewall. In Figure 11, the effect of sidewall angles on the reflectance of HCG is numerically calculated. As the sidewall angles decrease from 90° to 84°, the average reflectance drops from over 90% to less than 50%, because the HCG behaves more like a cone-shaped anti-reflection coating when the sidewall angle is small.

The optical efficiency of the dispersive element is important for the overall efficiency of the CPV system, so the reflectance of each layer of HCG should be as high as possible. Based on the discussion above, while the optical efficiency for the fabricated layer is about 60%, there are several possible improvements for a better HCG reflectance. The TiO_2 sputtering condition can be further optimized to generate the film with a higher index, less surface roughness and lower

optical loss. The dry etching recipes should be further adjusted for a better etching profile, making the grating straighter, [which can be achieved by adjusting the combination of gases \(C₄F₈, SF₆ and O₂\) to balance the etching and re-deposition process](#). The nanoimprint and lift-off process should be improved to avoid roughness and fabrication errors so that the unnecessary scattering can be reduced to increase the overall optical efficiency.

By stacking multiple layers of two-dimensional HCGs with different pitches, the dispersive mirror can operate in much broader spectrum. The mirror can reflectively direct light into different angles according to wavelengths, in a way of packaging all HCG layers subsequently in different tilting angles. Moreover, the dispersive mirror can be fabricated using nanoimprint lithography (NIL) in a large area and at a low cost. Moreover, the proposed system features an easy integration with existing concentrator photovoltaic (CPV) setup so it has the potential to be accepted widely by the industry to improve solar energy conversion efficiency.

DISCLOSURES:

The authors have nothing to disclose.

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